

a 2004 0250

The invention relates to semiconductor production technology, in particular to the obtaining of porous semiconductor structures.

The process for obtaining porous semiconductor structures consists in that onto the semiconductor surface there is applied a mask, onto the uncovered regions there are implanted high-energy ions, then the mask is removed and the semiconductor surface is subjected to the electrochemical pickling. Novelty consists in that before pickling onto the semiconductor surface there is applied a layer of photoresist material.

Claims: 1

Fig.: 2